AMENDMENTS TO THE SPECIFICATION

1) Please amend the paragraph spanning lines 5-7 of page 10, as follows:

Fig. 30A is a circuit diagram showing the structures of the prior art MOSFET improved to reduce the gate leak current; ~~and~~

2) After the paragraph spanning lines 8-10 of page 10, please insert:

Fig. 31 schematically shows the formation of a thick insulating film using furnace oxidation;

Fig. 32 schematically shows the removal of the thick insulating film formed on Fig. 31 from a part of an area of a silicon substrate;

Fig. 33 schematically shows the formation of a thin insulating film using a rapid thermal process; and

Fig. 34 is a flow chart depicting the steps which are carried out in Figs. 31 – 33.

3) Please amend the paragraph spanning lines 15-21 of page 33 as follows:

To overcome this problem, as show in Fig. [[29B]] 28B, a Schottky diode 11 formed of a metal/silicon layer is connected to the gate of the transistor of the present invention as shown in Fig. [[29A]] 28A, as a protective circuit. The breakdown voltage of this Schottky diode 11 is ~~determined~~ arranged to be lower than that of the transistor 9 of the present invention.